

SANYO Semiconductors DATA SHEET

ExPD(Excellent Power Device)

TND027MP— Lowside Power Switch Lamp-, Solenoid-, and Motor-Driving Applications

Features

- · N-channel MOSFET built in.
- · Overheat protection. (Self recovery type)
- · Overcurrent protection. (Self recovery type current limiting function)
- · Overvoltage protection.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDS		60	V
Output Current	I _O (DC)		1.5	А
Input Voltage	VIN		-0.3 to +10	V
Allowable Power Dissipation	PD		1.0	W
Operating Supply Voltage	V _{DS} (opr)		40	٧
Operating Temperature	Topr		-40 to +85	°C
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Clamp Voltage	V _{DS} , clamp	V _{IN} =0V, I _O =1mA	60			V
Output-OFF Current	IDSS(1)	V _{IN} =0V, V _{DS} =50V			10	μΑ
	I _{DSS} (2)	V _{IN} =0V, V _{DS} =12V			5	μΑ
Input Threshold Voltage	V _{IN} (th)	V _{DS} =5V, I _O =1mA	1.0	1.5	2.0	V
Protection Circuit Operating Input Voltage	VIN(opr)		4		10	V
Drain-to-Source ON Resistance	R _{DS} (on)	V _{IN} =5V, I _O =1A		0.3	0.4	Ω
Input Current (Output On)	I _{IN}	V _{IN} =5V			0.6	mA

Continued on next page.

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Over-Heat Detecting Temperature	Tj(sd)	V _{IN} =5V, I _O =1A	120	150	190	°C
Over-Current Detecting Current	Is	V _{IN} =5V	3.0	6.0	9.0	Α
Over-Current Limit (Peak)	ILMT	V _{IN} =5V	3.0	6.0	9.0	Α
Input Clamp Voltage	V _{IN} , clamp	I _{IN} =1mA	10			V

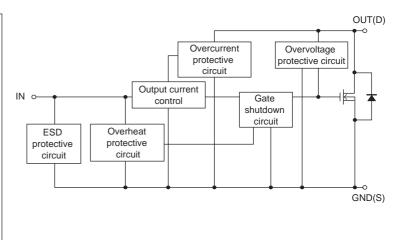
Notes: 1. Overcurrent protection circuit limits the output current to the range of overcurrent limit value.

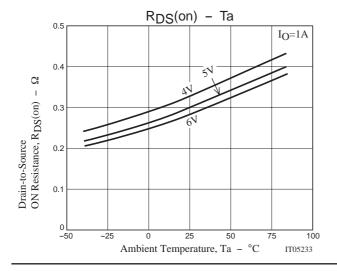
Package Dimensions

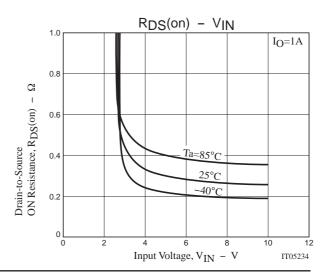
unit : mmm (typ) 7520-003

0.5 0.5 0.5 0.5 0.5 0.5 1 : GND 2 : OUT 3 : IN SANYO : MP

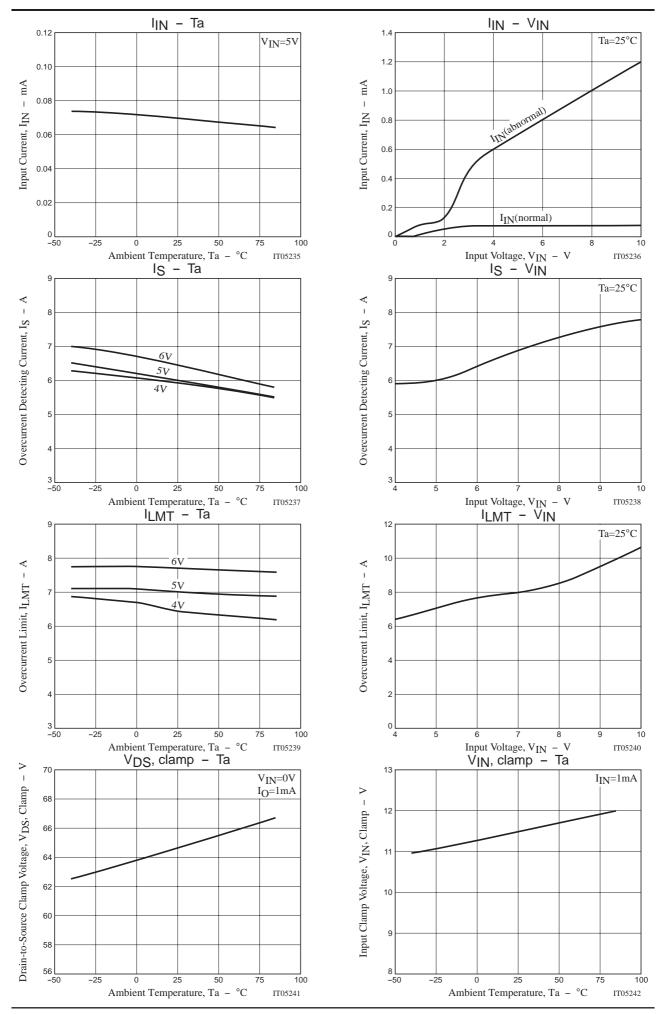
Block Diagram



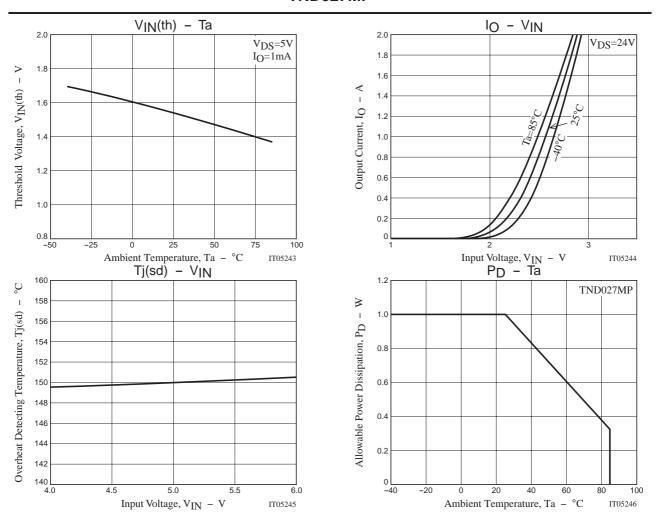




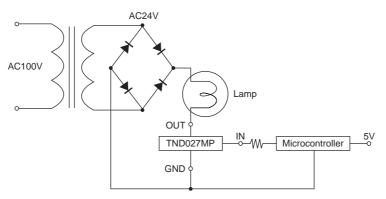
^{2.} During overheat protecting operation, output current is turned off.



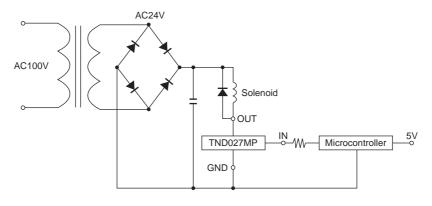
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Sample Application Circuit



Another Sample Application Circuit (Solenoid drive)



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Operation Description

- The output power MOSFET will be turned on when the input voltage exceeds the input threshold voltage (4 to 6V is recommended), and then the lamp will be turned on by the current flowing to the lamp. Conversely, the output power MOSFET will be turned off when the input voltage goes below the input threshold voltage, and the lamp will be turned off.
- The inrush current that occurs during normal lamp operation is limited to a preset value by the built-in overcurrent protecting circuit, which makes the lamp life longer.
- The internal overcurrent protection function limits the current of output power MOSFET when output current of at least the overcurrent detecting current value flows at load short. Besides, if the device temperature exceeds the allowable power dissipation, overheat protection function protects the power switch from being broken down by turning off the current of output power MOSFET when Tj comes to 150°C (typical).
- · As an example of application circuit, DC voltage can also be controlled as a solenoid drive.

Addition

- The diode between OUT and GND in the block diagram is parasitic diode of the MOSFET.
- Not apply a voltage on IN terminal during the period when OUT voltage is lower then GND voltage when driving a solenoid or a motor.
- Be sure connect a diode between OUT terminal and GND terminal when you want to apply a voltage on IN terminal under the above-stated state (that is, OUT Voltage < GND Voltage).

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